

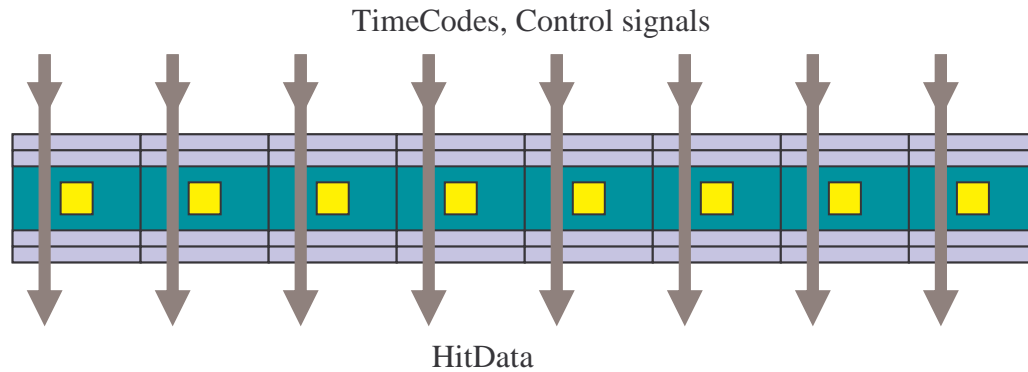
# Tera-Pixel APS for CALICE

Progress meeting, 17<sup>th</sup> May 2006

Jamie Crooks, Microelectronics/RAL

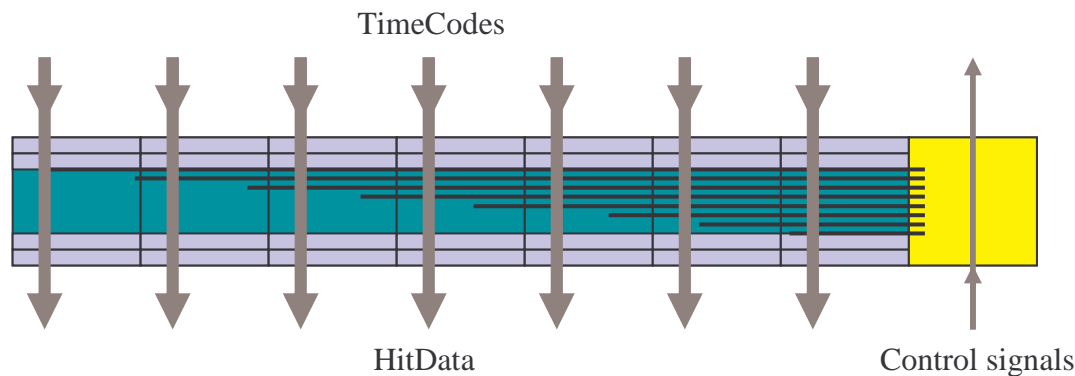
# Bump Bonding

- Gold stud + conductive glue
- 100um pads (may be able to bump to standard pad cells)
- Heat ( $>175^{\circ}$ ) + Pressure
- Hand alignment & trials à extra effort req'd
- Physical size may be problematic
  - 2inch hotplate
  - Would eventually need very large cavity reflow oven
- Indium requires special wafer processing



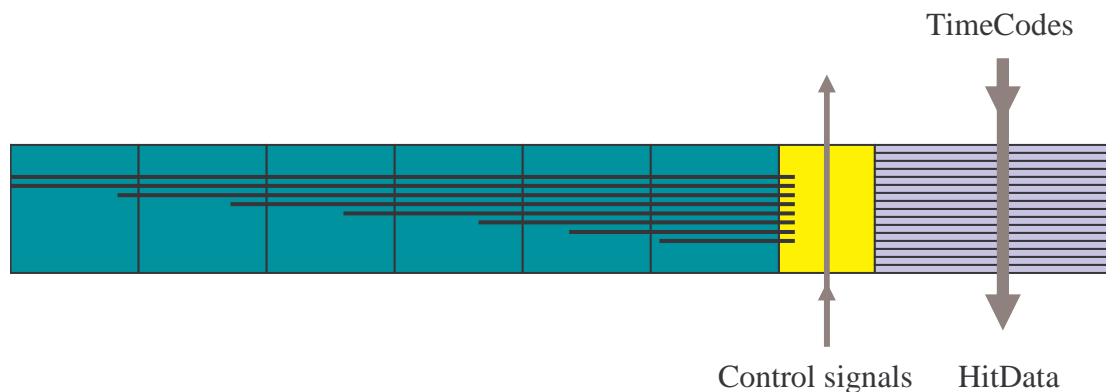
## Fully Independent pixels

- DRAMs only à max 4 regs per pixel
- Most regs not used
- Time code & data sense circuits required for every column (N)
- Control logic complex à large area
- Significant dead space in every pixel à poor charge collection



## Centralised controller

- DRAMs only à max 4 regs per pixel
- Time code & data sense circuits required for every column (N)
- +Complex control logic moved out of pixel
- Reduced dead space in every pixel à better charge collection
- Dead area ~6%



## Centralised memory + controller

- SRAMs can be used in dead areas
- Limited storage facility (calc overflow prob!)
- Only 1-in-N time code & data sense circuits
- +Complex control logic moved out of pixel
- Reduced dead space in every pixel à better charge collection
- Dead area ~6%

*See separate PowerPoint*

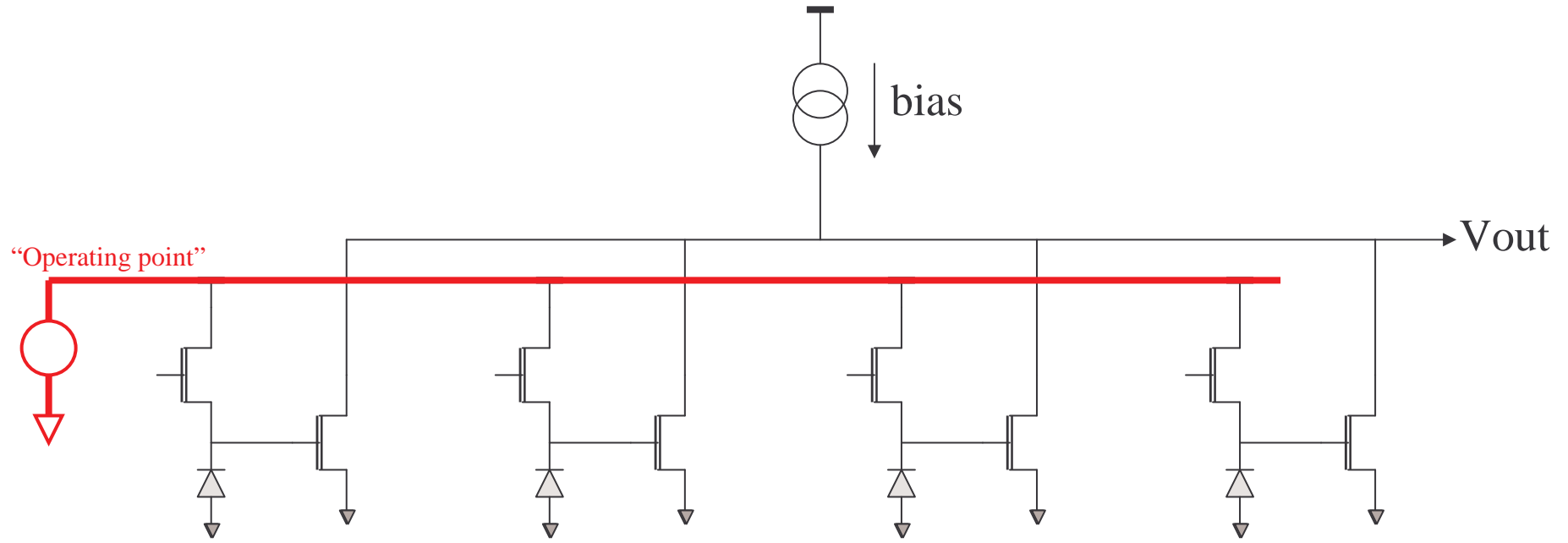
Key

 Pixels containing diodes

 Active Control logic

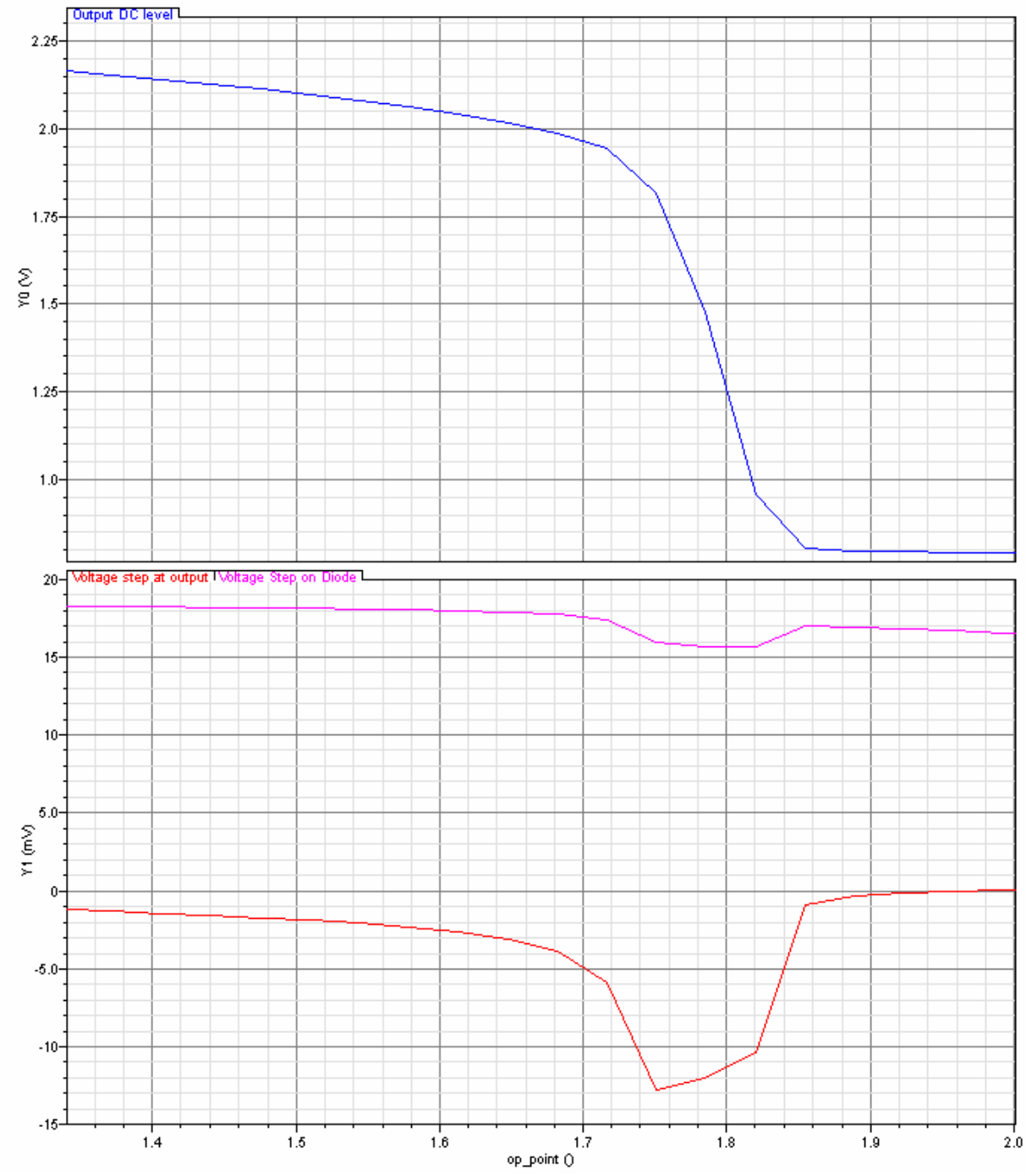
 Memory cells

# Analog Sum



# Analog Sum

450 electrons  
1 diode collects all  
Sweep diode reset point

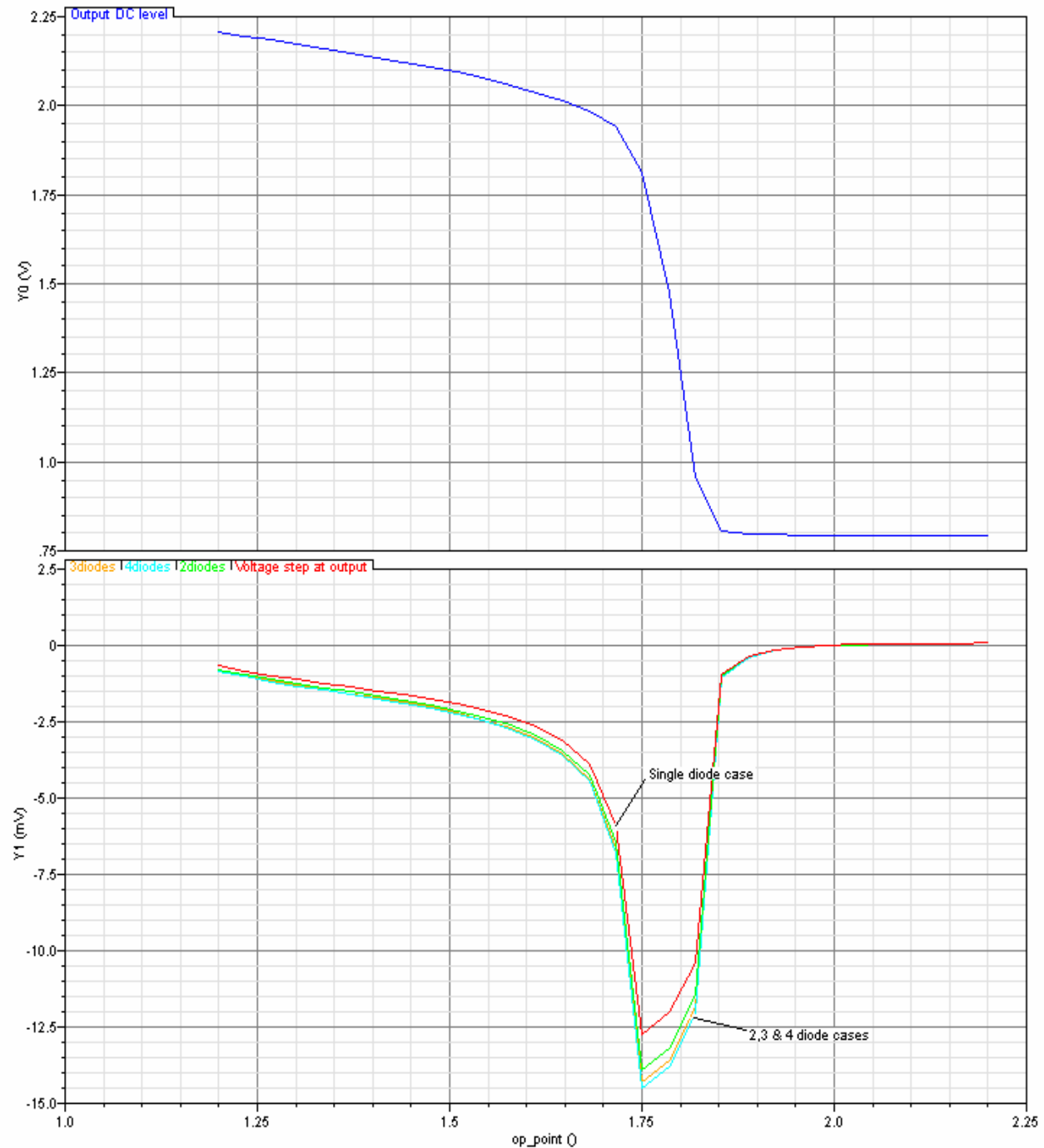


# Analog Sum

450 electrons

- 1 diode collects 450e
- 2 diodes collect 225e
- 3 diodes collect 150e
- 4 diodes collect 112e

Sweep diode reset point



# Analog Sum

450 electrons

- 4 diodes collect 112e

Sweep diode reset point

4 cases: bias currents

- 250nA
- 500nA
- 750nA
- 1uA

